

| NSN 5961-01-177-1332 Thyristor Semiconductor Device - Page 1 of 2 |
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| View Online at https://aerobasegroup.com/nsn/5961-01-177-1332 |
| Inclosure Material: |
| Metal |
| Overall Length: |
| 0.260 inches |
| Terminal Length: |
| 1.500 inches |
| Overall Diameter: |
| 0.370 inches |
| Internal Configuration: |
| Junction contact |
| Joint Electronic Device Engineering Council/jedec/case Outline Designation: |
| To-5 |
| Electrode Internally-electrically Connected To Case: |
| Anode |
| Mounting Method: |
| Terminal |
| Terminal Circle Diameter: |
| 0.200 inches |
| Features Provided: |
| Hermetically sealed case |
| Semiconductor Material: |
| Silicon |
| Voltage Rating In Volts Per Characteristic: |
| 2.2 forward voltage, peak and 1.0 gate trigger voltage, dc |
| Current Rating Per Characteristic: |
| 2.00 milliamperes forward current, total rms peak and 350.00 microamperes forward current, total rms preset |
| Maximum Operating Tempurature Per Measurement Point: |
| 125.0 degrees celsius ambient air |
| Special Features: |
| Junction pattern arrangement: pnpn |
| Precious Material And Location: |
| Terminal surfaces gold |
| Precious Material: |
| Gold |
| Terminal Type And Quantity: |
| 3 uninsulated wire lead |

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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